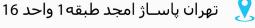






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RJH60F7ADPK

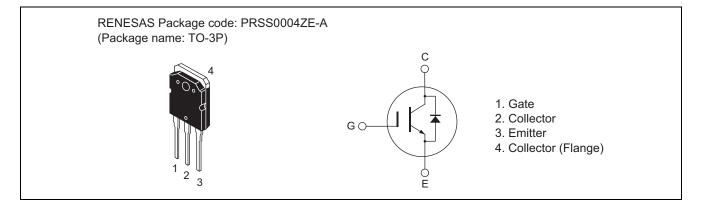
Silicon N Channel IGBT High Speed Power Switching

REJ03G1837-0100 Rev.1.00 Oct 13, 2009

Features

- High speed switching
- Low on-state voltage
- Fast recovery diode

Outline



Absolute Maximum Ratings

 $(Tc = 25^{\circ}C)$

Item		Symbol	Ratings	Unit
Collector to emitter voltage		V _{CES}	600	V
Gate to emitter voltage		V _{GES}	±30	V
Collector current	Tc = 25°C	Ic	90	Α
	Tc = 100°C	Ic	50	Α
Collector peak current		ic(peak) Note1	180	A
Collector to emitter diode forward peak current		i _{DF} (peak) Note2	100	A
Collector dissipation		Pc	328.9	W
Junction to case thermal impedance (IGBT)		θј-с	0.38	°C/W
Junction to case thermal impedance (Diode)		θј-с	2.0	°C/W
Junction temperature		Tj	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. Pulse width limited by safe operating area.

2. $PW \le 5 \mu s$, duty cycle $\le 1\%$

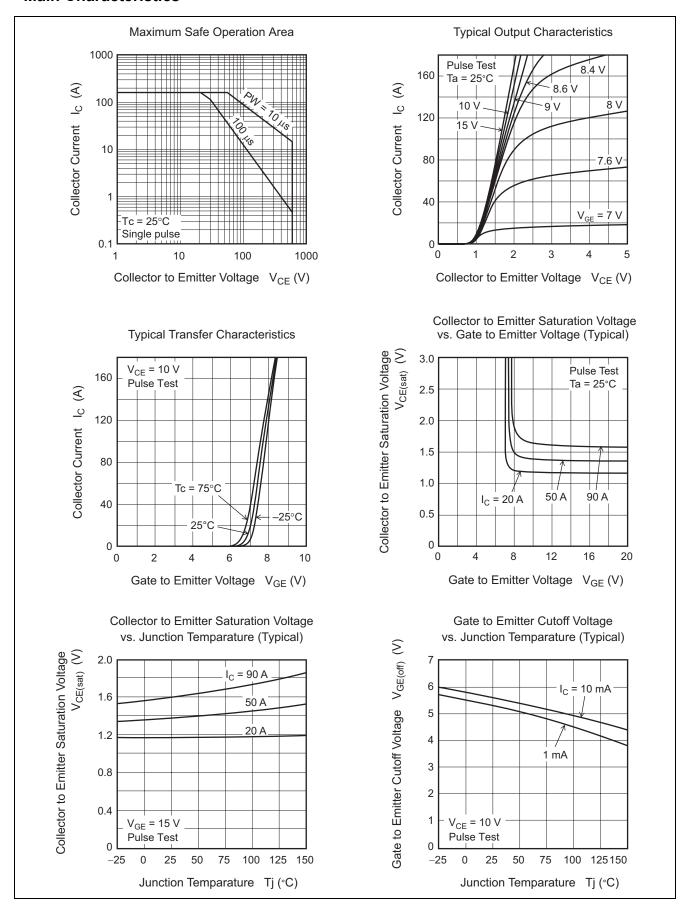
Electrical Characteristics

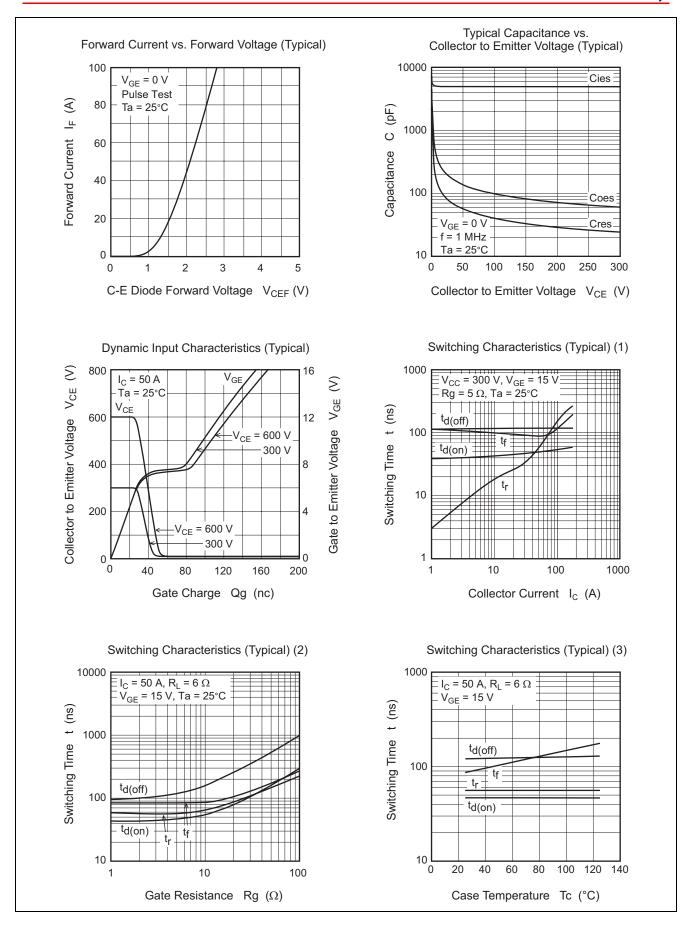
 $(Tj = 25^{\circ}C)$

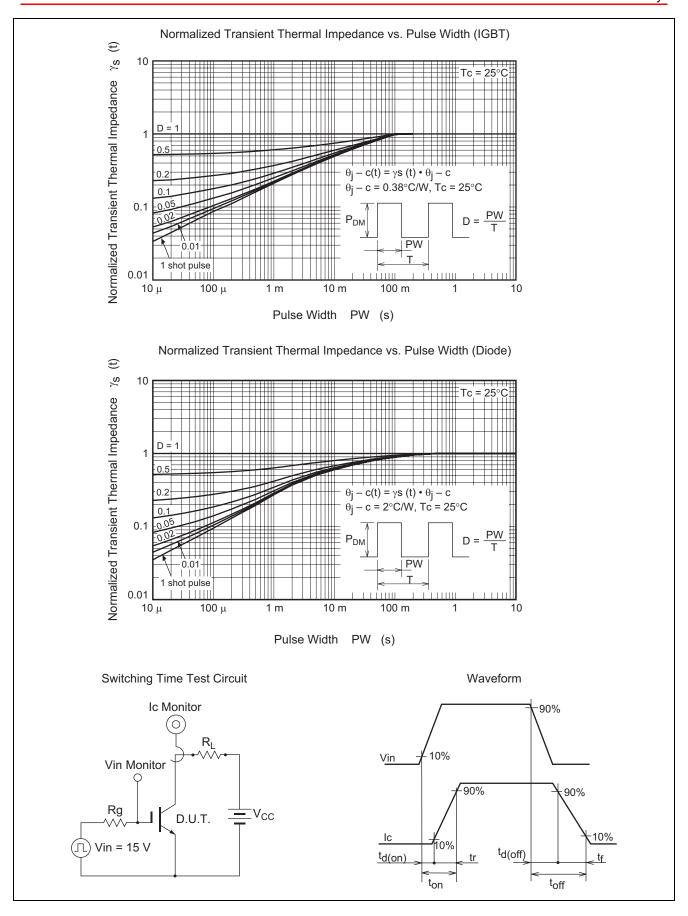
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current	I _{CES}	_	_	100	μΑ	$V_{CE} = 600V, V_{GE} = 0$
Gate to emitter leak current	I _{GES}	_	_	±1	μА	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{\text{GE(off)}}$	4	_	8	V	$V_{CE} = 10V, I_{C} = 1 \text{ mA}$
Collector to emitter saturation voltage	V _{CE(sat)}	_	_	1.75	V	$I_C = 50 \text{ A}, V_{GE} = 15V^{\text{Note3}}$
	V _{CE(sat)}	_	1.6	_	V	$I_C = 90 \text{ A}, V_{GE} = 15V^{\text{Note3}}$
Input capacitance	Cies	_	4890	_	pF	V _{CE} = 25 V
Output capacitance	Coes	_	198	_	pF	V _{GE} = 0 V
Reverse transfer capacitance	Cres	_	83	_		f = 1 MHz
Switching time	t _{d(on)}	_	48	_	ns	I _C = 30 A, Resistive Load
	t _r	_	36	_	ns	V _{CC} = 300 V
	t _{d(off)}	_	122	_	ns	V _{GE} = 15 V
	t _f	_	95	_	ns	Rg = 5 Ω Note3
C-E diode forward voltage	V _{ECF1}	_	1.6	2.1	V	I _F = 20 A ^{Note3}
C-E diode reverse recovery time	t _{rr}	_	140	_	ns	I _F = 20 A
						$di_F/dt = 100 A/\mu s$

Notes: 3. Pulse test

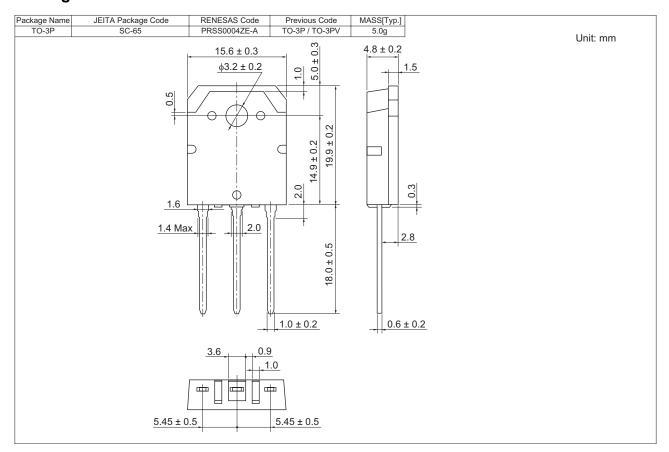
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJH60F7ADPK-00-T0	360 pcs	Box (Tube)

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